

Low Power 2-Channel Central-Office xDSL Driver

Check for Samples: [LMH6678](#)

FEATURES

- $AV_{CC1} = AV_{CC2} = +12V$, $AV_{DD} = DV_{DD} = +3.3V$, $T_A = 25^\circ C$, 2/3 Power Mode, Typical Values Unless Specified.
- Low Power Consumption
 - Line Power $P_{LINE} = 100 \text{ mW}$ 580 mW/Ch
 - No Signal 185 mW/Ch
 - Listen Mode 100 mW/Ch
 - Shutdown Mode 3 mW/Ch
- Power Supply
 - Analog (AV_{CC1} , AV_{CC2}) +12V
 - Digital (DV_{DD} , AV_{DD}) +3.3V
- Output Voltage Swing @ $R_L = 31\Omega$
 - Single Ended 11.5 V_{PP}
 - Differential 23 V_{PP}
- Multi Yone Power Ratio, $f = 500 \text{ kHz}$ 72 dB
- Output Current 580 mA
- Thermal Shutdown Protection
- 5mm x 4mm LLP Package
- Low Thermal Resistance 36°C/W (θ_{JA})
- Small PCB Footprint

APPLICATION

- Full Rate ADSL, ADSL+, ADSL++ or G. Lite Linecard
- Remote DSLAMs

DESCRIPTION

The LMH6678 is a low power 2-channel differential output driver utilizing dual current feedback op amps with a fixed gain of $A_V = +5.4$.

The LMH6678 utilizes high integration with low power consumption to provide 580 mW at 19.8 dBm line output. The LMH6678 can also be put into a listen mode to maintain the termination for receive signals with 100 mW/Ch power dissipation.

The LMH6678 has two separate 2-bit power control inputs compatible with 3.3V CMOS for each channel that enable independent control of line status. When the drivers for both channels are shut off, power consumption drops to only 6 mW.

Thermal Shutdown function protects the IC from a shorted line fault or system over temperature.

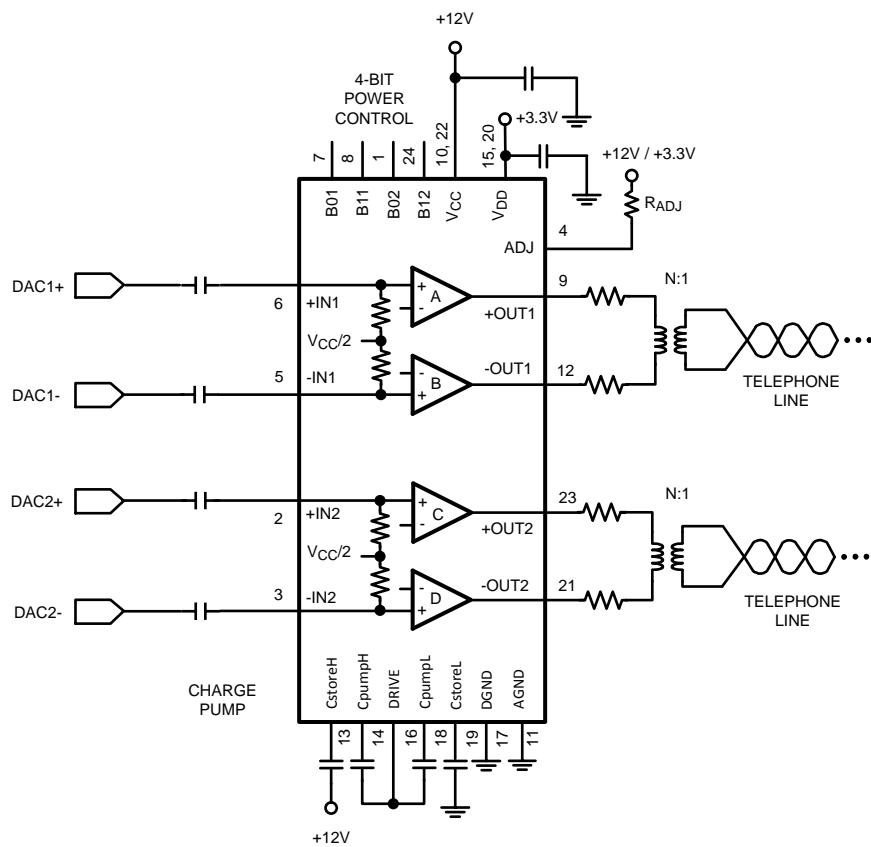
The LMH6678 is available in a 5mm x 4mm 24-lead LLP package.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

All trademarks are the property of their respective owners.

Block Diagram



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

Absolute Maximum Ratings⁽¹⁾⁽²⁾

ESD Tolerance	Human Body Model	2KV ⁽³⁾
	Machine Model	200V ⁽⁴⁾
V _{IN} Differential		±3V
Supply Voltages	A _V _{CC1} – AGND or A _V _{CC2} – AGND	+13.2V
	D _V _{DD} – DGND	+3.6V
	A _V _{DD} – AGND	+3.6V
	DGND – AGND	±0.2V
	A _V _{CC1} – A _V _{CC2}	±0.2V
	A _V _{DD} – D _V _{DD}	±0.2V
Voltage at Input Pin	Analog Input	A _V _{CC1} (A _V _{CC2}) +0.8V, AGND –0.8V
	Digital Control Input	D _V _{DD} +0.8V, DGND –0.8V
Soldering Information	Infrared or Convection (20 sec.)	235°C
Storage Temperature Range		-65°C to +150°C
Junction Temperature ⁽⁵⁾		+150°C

- (1) Absolute maximum ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not ensured. For ensured specifications and the test conditions, see the Electrical Characteristics.
- (2) If Military/Aerospace specified devices are required, please contact the Texas Instruments Sales Office/ Distributors for availability and specifications.
- (3) Human body model, 1.5kΩ in series with 100pF.
- (4) Machine Model, 0Ω in series with 200 pF.
- (5) The maximum power dissipation is a function of T_{J(MAX)}, θ_{JA}, and T_A. The maximum allowable power dissipation at any ambient temperature is P_D = (T_{J(MAX)} - T_A)/θ_{JA}. All numbers apply for packages soldered directly onto a PC board. Die attach pad is electrically connected to AGND.

Operating Ratings⁽¹⁾

Supply Voltage	A _V _{CC1} to AGND	+12V ±10%
	A _V _{CC2} to AGND	+12V ±10%
	D _V _{DD} to DGND	+3.3V ±10%
	A _V _{DD} to AGND	+3.3V ±10%
Operating Temperature Range ⁽²⁾⁽³⁾		-40°C to +85°C
Package Thermal Resistance (θ _{JA}) ⁽³⁾		36°C/W

- (1) Absolute maximum ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not ensured. For ensured specifications and the test conditions, see the Electrical Characteristics.
- (2) Continuous short circuit operation at elevated ambient temperature can result in exceeding the maximum allowed junction temperature of 150° C.
- (3) The maximum power dissipation is a function of T_{J(MAX)}, θ_{JA}, and T_A. The maximum allowable power dissipation at any ambient temperature is P_D = (T_{J(MAX)} - T_A)/θ_{JA}. All numbers apply for packages soldered directly onto a PC board. Die attach pad is electrically connected to AGND.

Electrical Characteristics

Unless otherwise specified, all limits ensured for $T_J = 25^\circ\text{C}$, $\text{AV}_{\text{CC}1} = \text{AV}_{\text{CC}2} = +12\text{V}$, $\text{DV}_{\text{DD}} = \text{AV}_{\text{DD}} = +3.3\text{V}$. $\text{DGND} = \text{AGND} = 0\text{V}$, 2/3 Power Mode. See⁽¹⁾.

Symbol	Parameter	Conditions	Min ⁽²⁾	Typ ⁽³⁾	Max ⁽²⁾	Units
Dynamic Performance						
f_{CL}	-3 dB BW	$R_L = 100\Omega$		50		MHZ
SR	Slew Rate ⁽⁴⁾	$V_{\text{IN_DIFF}} = \pm 2.4\text{V}$, $R_L = 100\Omega$		700		$\text{V}/\mu\text{s}$
Distortion and Noise Response						
HD2	2nd Harmonic Distortion	$f_c = 1 \text{ MHz}$, $V_O = 2 \text{ V}_{\text{PP}}$, $R_L = 31\Omega$		-91		dBc
		$f_c = 200 \text{ kHz}$, $V_O = 2 \text{ V}_{\text{PP}}$, $R_L = 31\Omega$		-98		
HD3	3 rd Harmonic Distortion	$f_c = 1 \text{ MHz}$, $V_O = 2 \text{ V}_{\text{PP}}$, $R_L = 31\Omega$		-57		dBc
		$f_c = 200 \text{ kHz}$, $V_O = 2 \text{ V}_{\text{PP}}$, $R_L = 31\Omega$		-71		
MTPR	Multi-Tone Power Ratio	$f = 500 \text{ kHz}$		72		dBc
V_{IN}	Differential Output Noise	100 kHz to 10 MHz		57		$\text{nV}/\sqrt{\text{Hz}}$
Input Characteristics						
V_{IN}	Input DC Voltage	Common Mode	6.04	6.1	6.16	V
R_{IN}	Input Resistance	Differential $I_{\text{DIFF}} = 10 \mu\text{A}$ from $+\text{IN}$ to $-\text{IN}$	14.4	20	28.4	$\text{k}\Omega$
Transfer Characteristics						
A_V	Voltage Gain	$V_{\text{IN_DIFF}} = -1$ to 1V , No Load	+5.37	+5.40	+5.48	V/V
PSRR	Power Supply Rejection Ratio			-108		dB
Xt	Cross Talk	$f = 1 \text{ MHz}$, $R_L = 100\Omega$		-95		
V_O	Output Voltage Swing High	$V_{\text{IN_DIFF}} = \pm 2.4\text{V}$, No Load		11.85		V
		$V_{\text{IN_DIFF}} = \pm 2.4\text{V}$, $R_L = 31\Omega$	11.68	11.75		
		$V_{\text{IN_DIFF}} = \pm 2.4\text{V}$, $I_{\text{OUT}} = 580 \text{ mA}$	11.64	11.74		
	Output Voltage Swing Low	$V_{\text{IN_DIFF}} = \pm 2.4\text{V}$, No Load		0.15		V
		$V_{\text{IN_DIFF}} = \pm 2.4\text{V}$, $R_L = 31\Omega$		0.25	0.36	
		$V_{\text{IN_DIFF}} = \pm 2.4\text{V}$, $I_{\text{OUT}} = 580 \text{ mA}$		0.31	0.39	
I_{SC}	Output Short Circuit Current	Sourcing to Ground		+800		mA
		Sinking to Ground		-800		
I_{OUT}	Output Current	$V_{\text{IN_DIFF}} = \pm 2.4\text{V}$ Sourcing, $R_L = 20\Omega$ Sinking, $R_L = 20\Omega$		± 580		mA
V_{OC}	Output Common Mode Voltage		5.89	6	6.05	V
V_{OS}	Output Offset Voltage		-40	0	+40	mV
Power Supply⁽⁵⁾⁽⁶⁾						
I_{CC}	AV _{CC} Quiescent Supply Current	B01	B11	B02	B12	
	Full Power	L	L	L	28.6	33
	2/3 Power	H	L	H	18.6	22
	1/3 Power	L	H	L	9.2	12
	Shutdown	H	H	H		.02

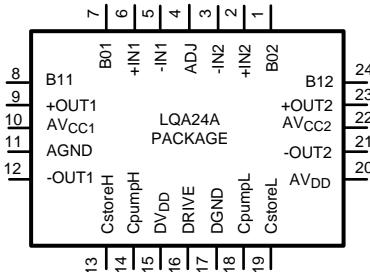
- (1) Electrical table values apply only for factory testing conditions at the temperature indicated. Factory testing conditions result in very limited self-heating of the device such that $T_J = T_A$. No specification of parametric performance is indicated in the electrical tables under conditions of internal self heating where $T_J > T_A$. Absolute maximum ratings indicate junction temperature limits beyond which the device may be permanently degraded, either mechanically or electrically.
- (2) All limits are guaranteed by testing or statistical analysis.
- (3) Typical Values represent the most likely parametric norm.
- (4) Slew rate is the slowest of the rising and falling slew rates.
- (5) Quiescent supply current specification apply for the condition of no input signal. See [Application Notes](#) for information on power consumption as a function of output power, power control bit settings and external resistor R_{ADJ} .
- (6) "L" is V_{IL} and "H" is V_{IH} .

Electrical Characteristics (continued)

Unless otherwise specified, all limits ensured for $T_J = 25^\circ\text{C}$, $\text{AV}_{\text{CC}1} = \text{AV}_{\text{CC}2} = +12\text{V}$, $\text{DV}_{\text{DD}} = \text{AV}_{\text{DD}} = +3.3\text{V}$. $\text{DGND} = \text{AGND} = 0\text{V}$, 2/3 Power Mode. See⁽¹⁾.

Symbol	Parameter	Conditions				Min ⁽²⁾	Typ ⁽³⁾	Max ⁽²⁾	Units
I_{DV}	DV_{DD} Quiescent Supply Current	B01	B11	B02	B12				mA
	Full Power	L	L	L	L	11	16	19	
	2/3 Power	H	L	H	L	7	12	15	
	1/3 Power	L	H	L	H	3	7	10.3	
	Shutdown	H	H	H	H		0.05	.14	
I_{AV}	AV_{DD} Quiescent Supply Current	All Power Modes				.8	1.1	1.4	mA
Logic Inputs									
V_{IH}	Input High Voltage					2.7	3.3		V
V_{IL}	Input Low Voltage						0	0.5	V
I_{IH}	Input High Current	@ $V_{\text{IH}} = 3.3\text{V}$				-0.5	0.02	+0.5	μA
I_{IL}	Input Low Current	@ $V_{\text{IH}} = 0\text{V}$				-0.5	0.02	+0.5	μA
Charge Pump									
f_{CP}	Charge Pump Frequency	Measure at DRIVE at Full Power				2.43	2.75		MHz
V_{HIGH}	Charge Pump High Average Voltage	Measure at CstoreH at Full Power					+14.6		V
V_{LOW}	Charge Pump Low Average Voltage	Measure at CstoreL at Full Power					-2.7V		V

Connection Diagram



Note: Die attach pad is electrically connected to AGND

Typical Performance Characteristics

Single-Ended Small Signal Frequency Response
@ $R_L = 100\Omega$

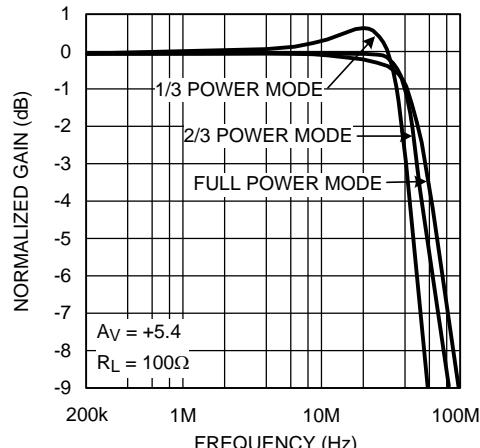


Figure 1.

Single-Ended Small Signal Frequency Response
@ $R_L = 36\Omega$

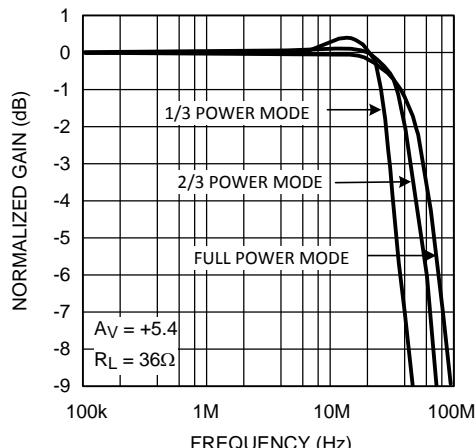


Figure 2.

Medium Signal Pulse Response
@ $R_L = 100\Omega$, 1 MHz

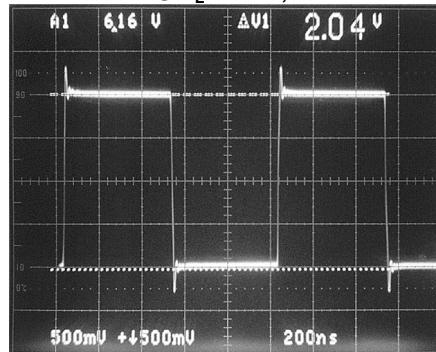


Figure 3.

Medium Signal Pulse Response
@ $R_L = 36\Omega$, 1 MHz

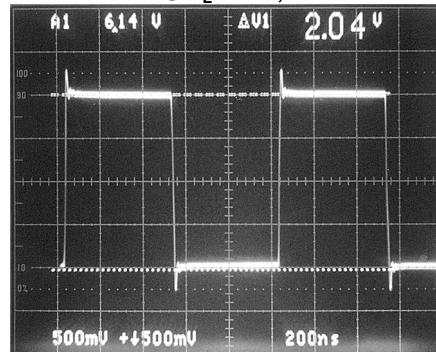


Figure 4.

Large Signal Pulse Response
@ $R_L = 100\Omega$, 1 MHz

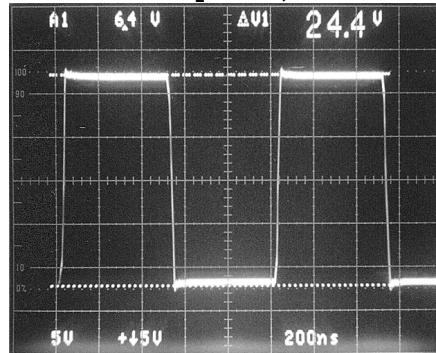


Figure 5.

Large Signal Pulse Response
@ $R_L = 36\Omega$, 1 MHz

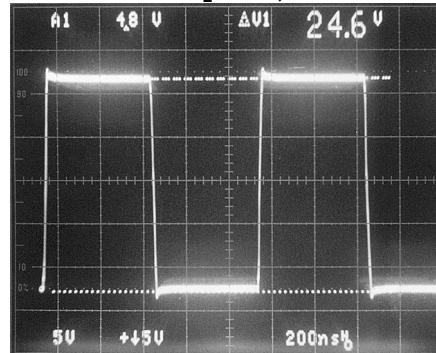


Figure 6.

Typical Performance Characteristics (continued)

Single-Ended Small Signal Frequency Response
@ $Z_L = 100\Omega||100\text{ pF}$

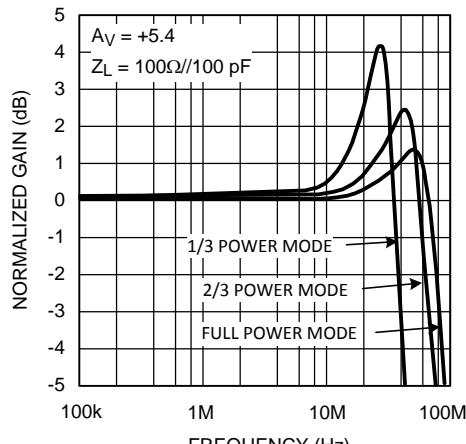


Figure 7.

Single-Ended Small Signal Frequency Response
@ $Z_L = 36\Omega||100\text{ pF}$

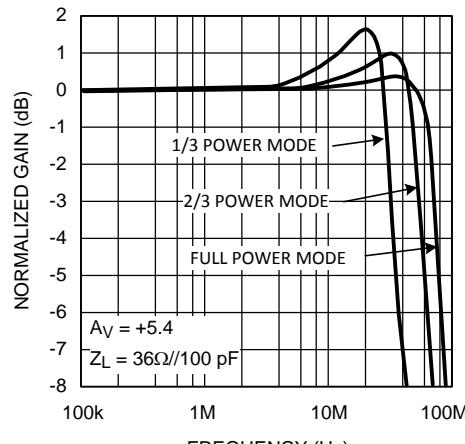


Figure 8.

Output Swing @ $Z_L = 100\Omega||100\text{ pF}$, 1 MHz

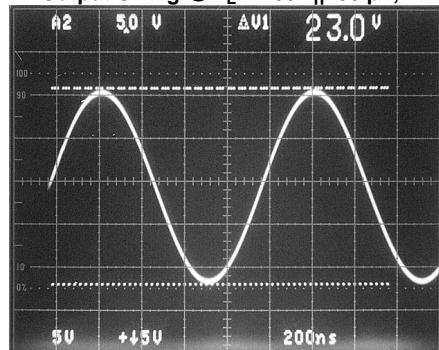


Figure 9.

Output Swing @ $Z_L = 36\Omega||100\text{ pF}$, 1 MHz

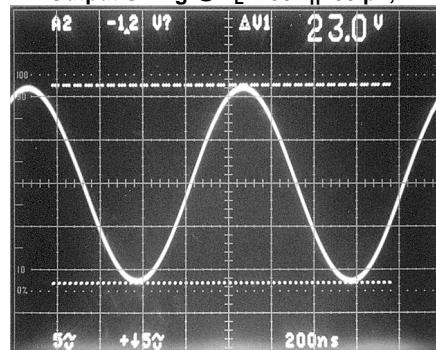


Figure 10.

Output Swing @ $Z_L = 100\Omega||100\text{ pF}$, 5 MHz

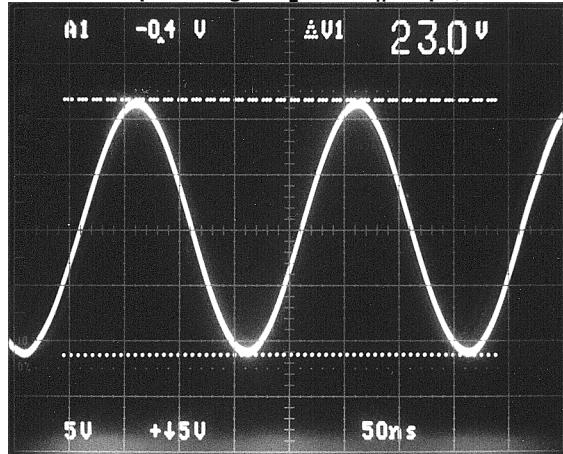


Figure 11.

Output Swing @ $Z_L = 36\Omega||100\text{ pF}$, 5 MHz

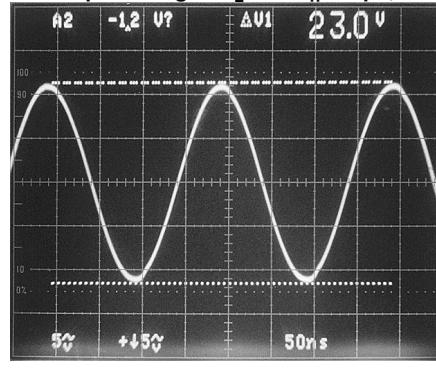


Figure 12.

Typical Performance Characteristics (continued)

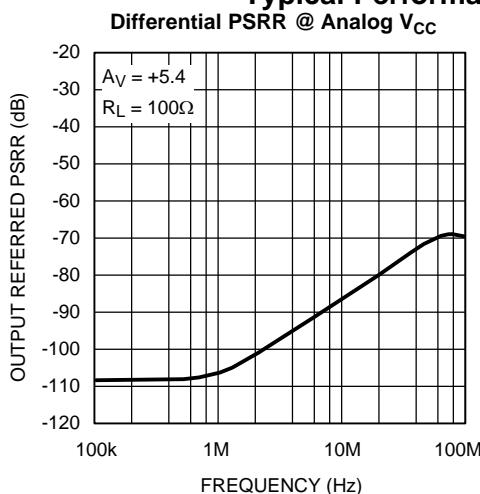


Figure 13.

Differential Output Referred Cross Talk

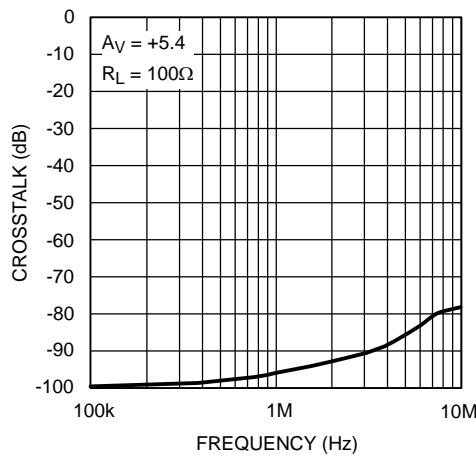


Figure 14.

Charge Pump @ Drive Pin

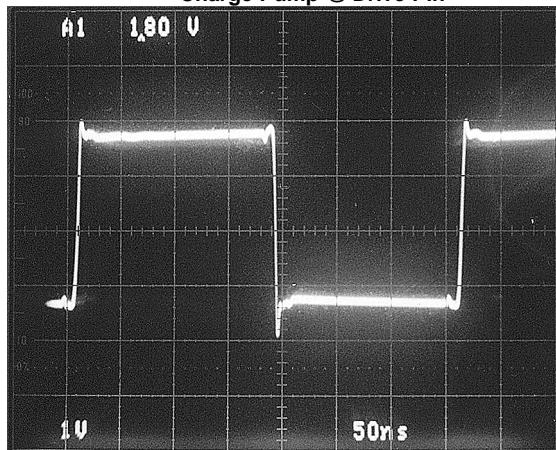


Figure 15.

Charge Pump Leakage (Differential)

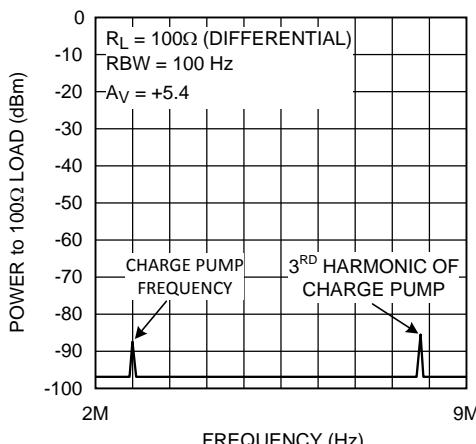


Figure 16.

Output Voltage Noise @ $R_S = 50\Omega$

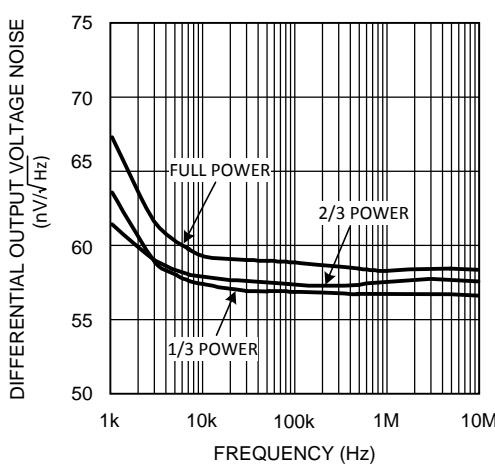


Figure 17.

Output Voltage Swing

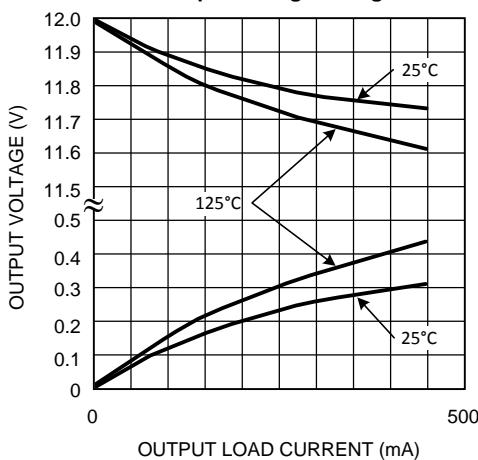
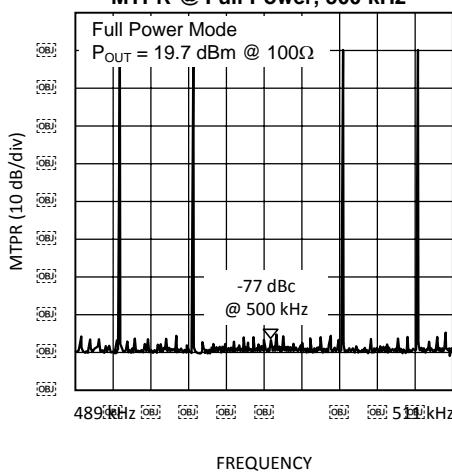
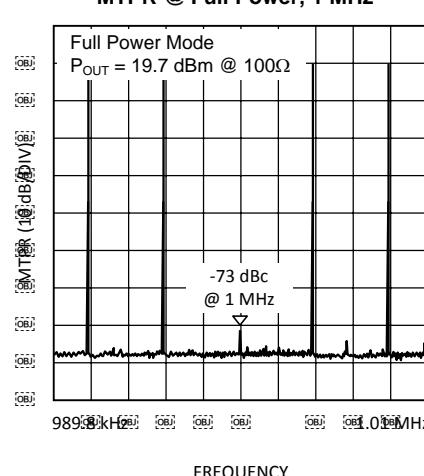
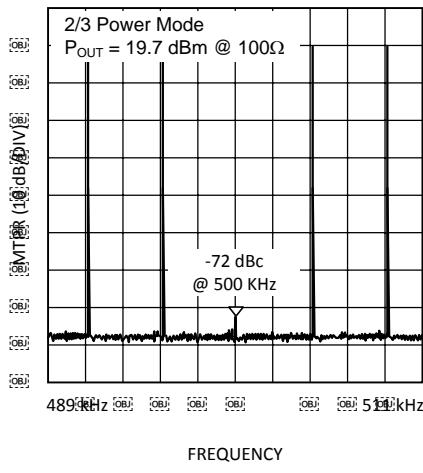
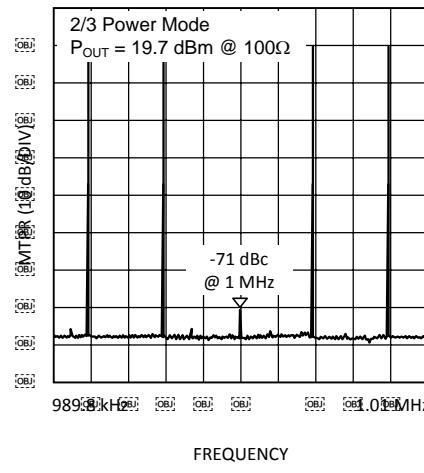
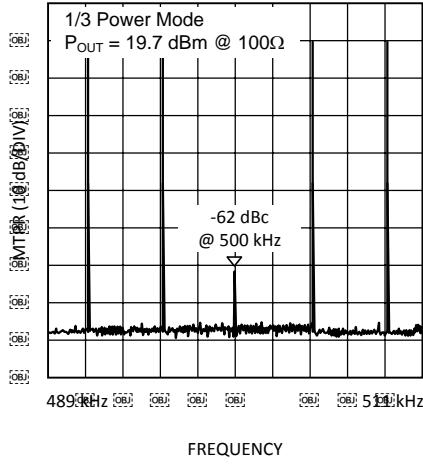
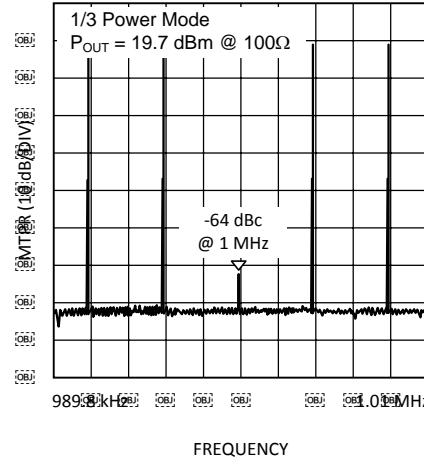


Figure 18.

Typical Performance Characteristics (continued)
MTPR @ Full Power, 500 kHz

Figure 19.
MTPR @ Full Power, 1 MHz

Figure 20.
MTPR @ 2/3 Power, 500 kHz

Figure 21.
MTPR @ 2/3 Power, 1 MHz

Figure 22.
MTPR @ 1/3 Power, 500 kHz

Figure 23.
MTPR @ 1/3 Power, 1 MHz

Figure 24.

Typical Performance Characteristics (continued)

Detail View of Total I_{CC} vs. R_{ADJ} @ $V_{ADJ} = +12V$

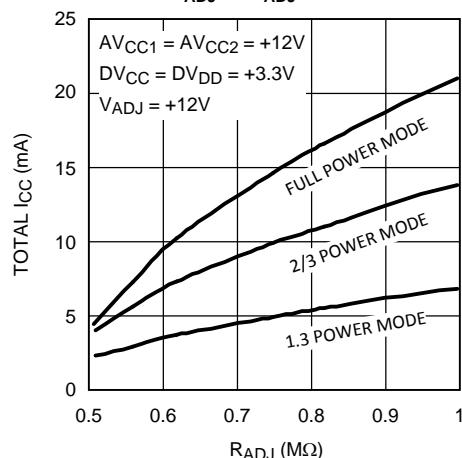


Figure 25.

Detail View of Total I_{CC} vs. R_{ADJ} @ $V_{ADJ} = +3.3V$

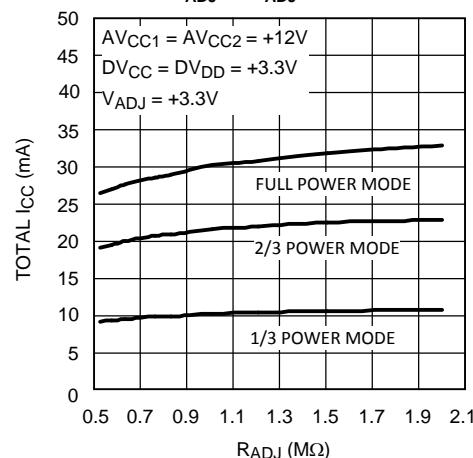


Figure 26.

Harmonic Distortion vs. Frequency

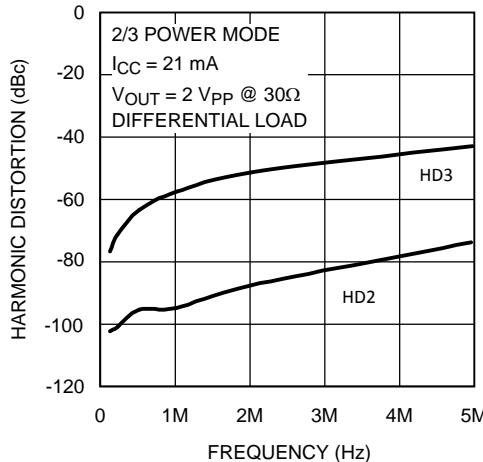


Figure 27.

Harmonic Distortion vs. Load

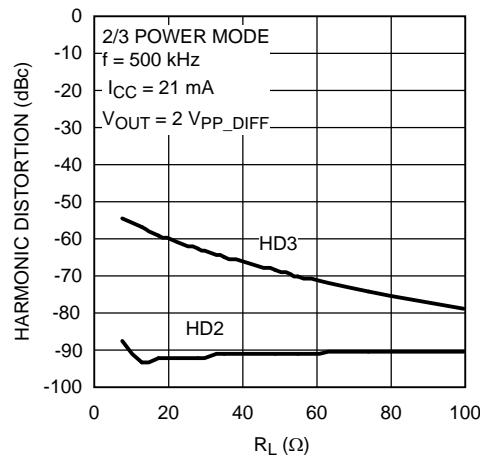


Figure 28.

Harmonic Distortion @ $I_{CC} = 33mA$, 200 kHz

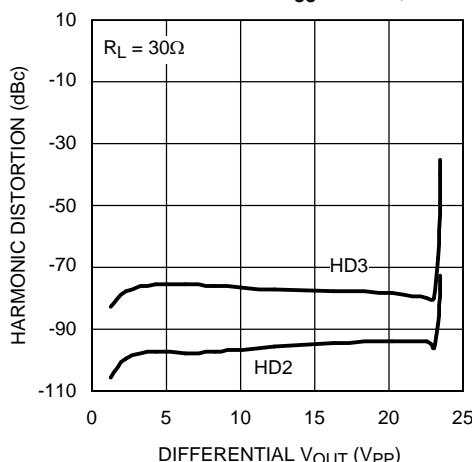


Figure 29.

Harmonic Distortion @ $I_{CC} = 33 mA$, 1 MHz

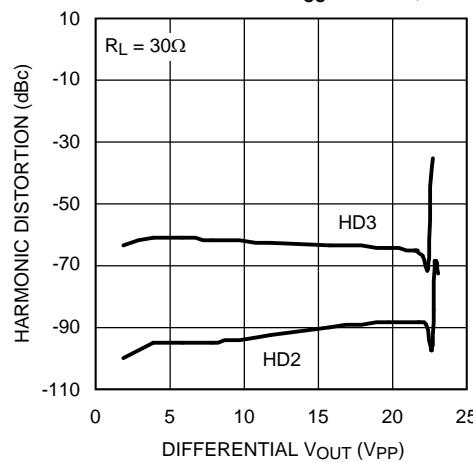


Figure 30.

Typical Performance Characteristics (continued)

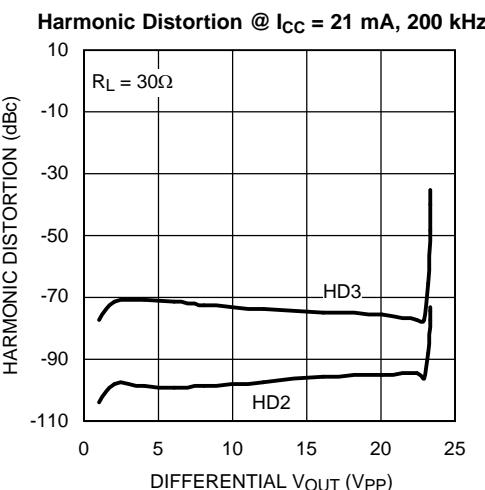


Figure 31.

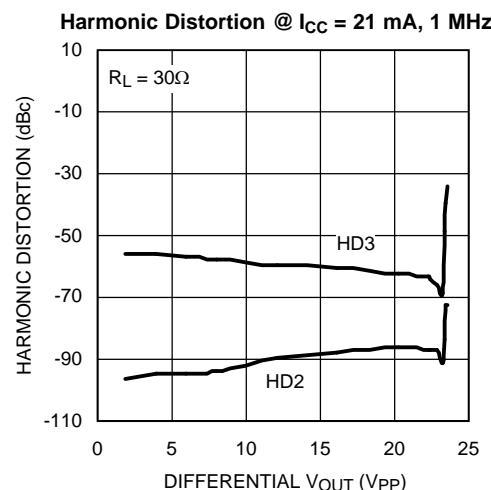


Figure 32.

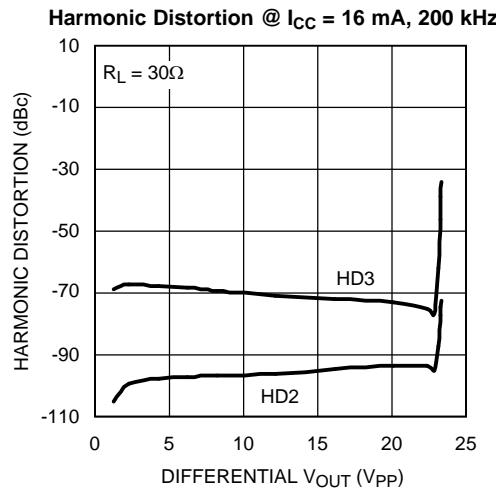


Figure 33.

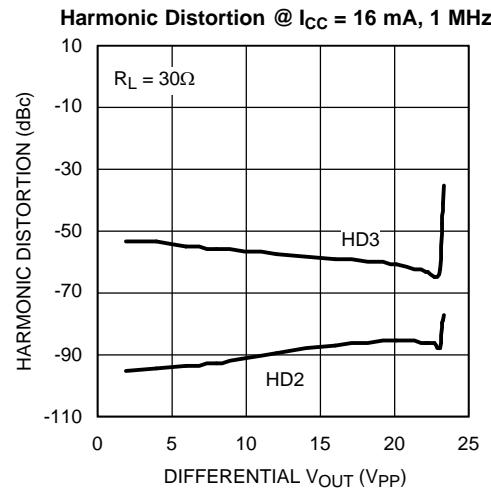


Figure 34.

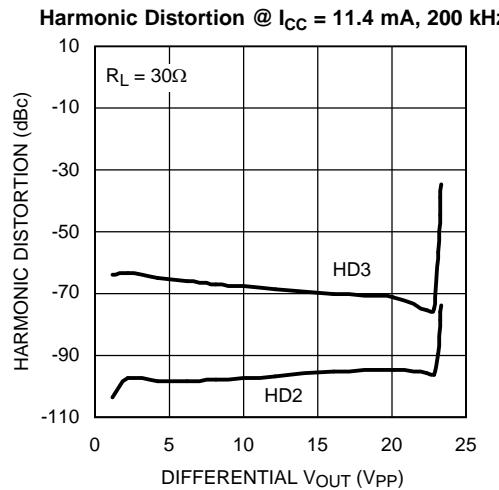


Figure 35.

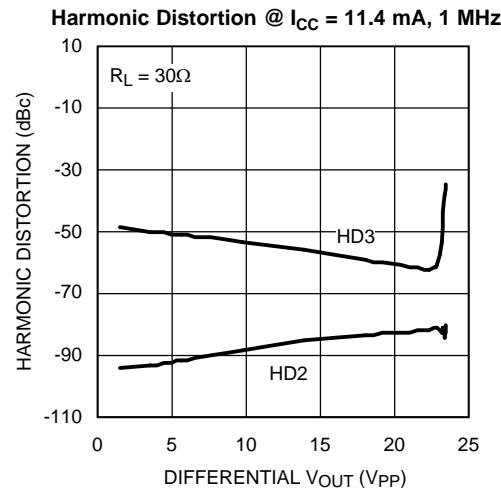


Figure 36.

APPLICATION NOTES

FUNCTIONAL DESCRIPTION

The LMH6678 contains two pairs of high speed/high output current operational amplifiers configured as two amplifiers differential inputs and outputs, as shown in Figure 37. Quiescent current can be set independently for each channel via two control bits as depicted in Table 1. Also, quiescent current can be continuously varied by selection of an external resistor between the ADJ pin and a supply voltage of either +12V or +3.3V.

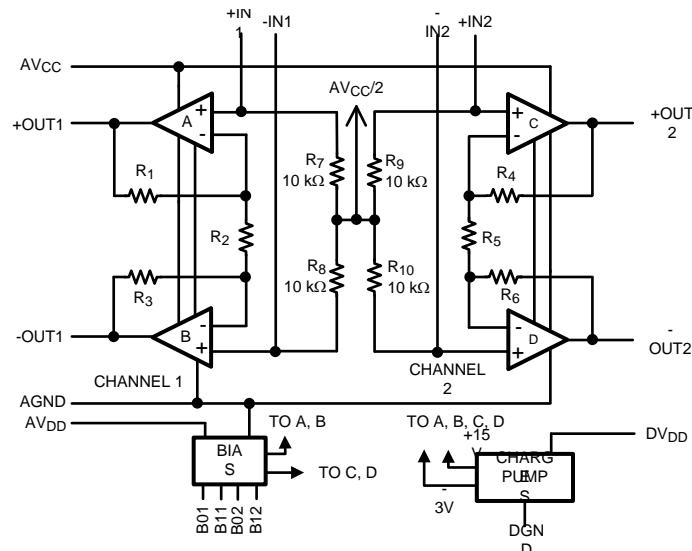


Figure 37. Functional Block Diagram

Table 1. Power Mode Logic Control

Power Mode	Channel A (B)	
	B01 (B02)	B11 (B12)
Full Power	L	L
2/3 Power	H	L
1/3 Power	L	H
Shutdown	H	H

Two supply voltages are required, $+12V \pm 10\%$ and $+3.3V \pm 10\%$. Current for the driver amplifiers, including their output current, flows from the 12V analog V_{CC} (AV_{CC}) supply and Analog Ground (AGND.) For proper output swing and distortion performance, both AV_{CC} pins must be connected to $+12V$ and the exposed metal pad must be soldered to ground potential as described in the [HIGH SPEED DRIVER LAYOUT GUIDELINES](#) section. Both AV_{DD} and DV_{DD} pins must be connected to $+3.3V$. The internal bias circuitry is powered from AV_{DD} and AGND while the digital circuitry and charge pump are powered from DV_{DD} and DGND. This allows separate bypassing and decoupling for AV_{DD} and DV_{DD} .

All supply voltage pins need a $0.1 \mu F$ ceramic capacitor in parallel with a $4.7 \mu F$ capacitor as bypass capacitors. The $0.1 \mu F$ capacitor should be as close as possible to the supply voltage pin and the larger capacitor placed next to it.

The LMH6678 delivers very low power consumption at a single $+12V$ analog supply voltage by a combination of its circuit architecture and the on-chip dual charge pump. The output stage is an emitter-follower type, which can provide low distortion, low quiescent current and high peak output currents.

The charge pumps generate two internal dc voltages, $V_{HIGH} = +15V$ and $V_{LOW} = -3V$. As shown in Figure 38, V_{HIGH} and V_{LOW} supply base currents for the output stages. This enables the drivers to swing within a $V_{CE(sat)}$ of V_{CC} and ground, giving the LMH6678 its high swing of $+11.5 V_{PP}$ into a 31Ω load.

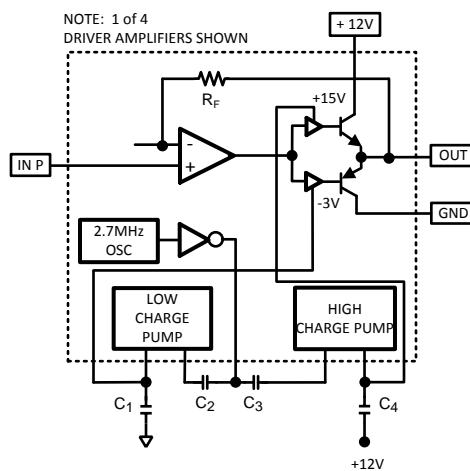


Figure 38. Internal Connections of Integrated Charge Pumps

CHARGE PUMPS

Figure 39 is a simplified schematic of the internal charge pumps. Each pump consists of a transfer capacitor and a reservoir capacitor and switches. The states of switches are driven by an internal 2.75 MHz clock oscillator. The transfer capacitor of the high charge pump, C_1 , is connected across V_{DD} and DGND during one phase of the clock and between V_{HIGH} and V_{CC} during the opposite phase. This causes its reservoir capacitor, C_2 , to charge up to V_{DD} (3.3Volts) potential less a small drop due to finite switch resistance. V_{HIGH} therefore is pumped to nearly $V_{CC} + V_{DD}$ potential or approximately +15V.

Similarly, the transfer capacitor of the low charge pump, C_3 , is connected across V_{DD} and DGND during one phase of the clock and between AGND and V_{LOW} during the opposite phase. This causes its reservoir capacitor, C_4 , to charge up to V_{DD} potential less a small drop due to finite switch resistance. V_{LOW} therefore is pumped to nearly $-V_{DD}$ potential or approximately -3V.

The charge pumps outputs provide both dc bias currents and the base current of the output transistors. These base currents are small compared to the dc bias currents. Typical and maximum quiescent V_{DD} supply currents are given in the electrical characteristics. Thus, for the charge pump capacitors C_1 - C_4 , the suggested values are 0.022 μ F 20% X7R type. With these values, the ripple on V_{HIGH} and V_{LOW} will be approximately 40 mV_{PP}. This results in a small spurious output on the line of typically -120 dBm/Hz at 2.75 MHz. Spurs produced at harmonics of the clock frequency are at least 20 dB lower and further attenuated by the transformer. This is shown in the [Typical Performance Characteristics](#) section. Ripple and spurious outputs can be further attenuated by increasing the size of the reservoir capacitors C_2 and C_4 .

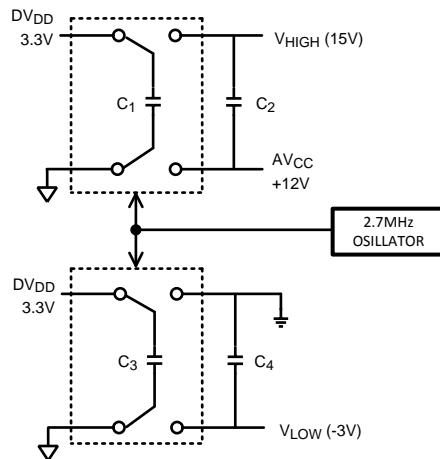


Figure 39. Charge Pump Functional Schematic

MULTI-TONE POWER RATIO AND NOISE

The Multi-Tone Power Ratio of the LMH6678 is shown in the [Typical Performance Characteristics](#) section. MTPR is the best representation of non-linearity for ADSL modems. The measurement is accomplished with all ADSL bins transmitting full power except one. The delta between the peak amplitude of the transmitting carriers and energy left in the single bin defines the maximum available SNR for that bin. The test circuit is described in [Figure 40](#). Here R_2 , C_3 , R_4 and C_4 were added for increase gain.

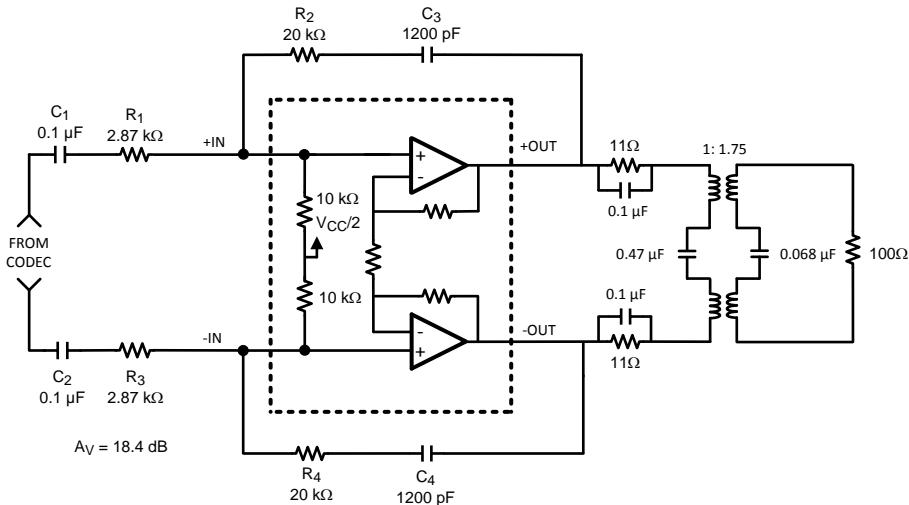


Figure 40. MTPR Measurement Test Circuit

R-C TERMINATION CIRCUIT AND TRANSFORMER TURNS RATIO

The LMH6678 was designed to operate in the circuit of [Figure 41](#). In this circuit, resistor R_1 and R_2 provide a line termination in the upstream band. At higher frequencies in the downstream band, capacitors C_1 and C_2 bypass R_1 and R_2 for higher efficiency.

To calculate the transformer turns ratio required, we assume a peak-to-rms ratio of 5.8 must be supported and the V_{CC} supply tolerance is 5%. At a 30Ω load, the driver outputs can swing to 350 mV of each rail with low distortion. This gives a peak swing of $12(0.95) - 0.7 = 10.7V$. A typical selection for C_1 , C_2 , R_1 and R_2 results in approximately 0.1 dB loss and the transformer loss is typically 0.25 dB, so total voltage loss is about 0.35 dB.

For 19.8 dBm output, line rms voltage is 3.09 and peak voltage is 17.9. The optimum turns ratio is calculated at $1.035 \times 17.9/10.7 = 1.73$. This gives a reflected line impedance of $100\Omega/(1.73)^2 = 33.4$ at the primary side. R_1 and R_2 are usually chosen to be $33.4/2 = 16.7$ to terminate the line at lower frequencies.

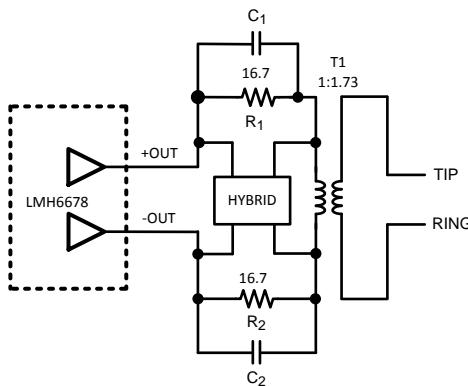


Figure 41. Typical R-C Termination

INPUT POWER LEVEL AND GAIN

With losses included, output power from the LMH6678 should be $19.8 \text{ dBm} + 0.35 \text{ dB} = 20.15 \text{ dBm}$ or 103.5 mW. At 33.4Ω , the rms differential output voltage is $\sqrt{P \times R} = 1.86 \text{ Vrms}$. The driver amplifiers have a voltage gain of 5.4V/V, so the input level should be $1.86/5.4 = 344 \text{ mV}_{\text{RMS}}$ to deliver 19.8 dBm to the line.

The driver input equivalent circuit is shown in [Figure 37](#). The inputs should be capacitively coupled to maintain the input and output common-mode voltage at $V_{\text{CC}}/2$.

If additional gain is required, the gain can be increased with positive feedback using the circuit of [Figure 42](#). In this case the voltage gain A_V will be

$$A_V = 5.4 * (1 - K) / (1 - 5.4 * K)$$

where

- $K = (R_1 || 10K) / (R_1 || 10K + R_2) = 10K * R_1 / (10K * R_1 + R_1 * R_2 + 10K * R_2)$
- $R_1 = R_3$
- $R_2 = R_4$

(1)

It is suggested to choose $R_1 < 3K$ so that the 15% tolerance of the input resistance will not greatly affect the gain. Furthermore, this circuit will have a differential input resistance of

$$R_{\text{IN_DIFF}} = 2 * R_1 - 2 * R_2 / (4.4) \quad (2)$$

which may be negative in band. Usually no stability problems are seen if this $|R_{\text{IN}}|$ is chosen larger than 500Ω . To minimize distortion caused by loading on the Codec outputs, $|R_{\text{IN}}|$ is usually chosen to be $1k\Omega$ or more. Additional blocking capacitors C_3 and C_4 must be inserted in series with R_2 and R_4 to prevent the circuit from latching. C_3 and C_4 should be chosen to be less than 1/5 of C_1 to avoid large signal oscillation.

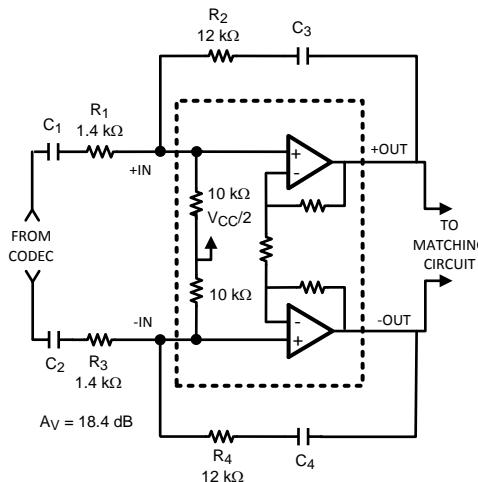


Figure 42. Increasing Gain

ACTIVE TERMINATION CIRCUIT

The LMH6678 can be used to synthesize the output impedance by using positive feedback to increase the output resistance. In ADSL this technique is often used to lower the total power consumption of the line driver by reducing the voltage across the series termination resistors. This approach gives slightly higher power consumption but better return loss in the downstream band compared to the R-C termination of [Figure 41](#). The equations that follow and [Figure 43](#) describe how to implement this technique with the LMH6678.

1. Pick positive feedback factor (also called the resistance gain), A_Z .
2. Pick desired output resistance, R_{OUT} , seen by the line.
3. Calculate transformer turns ratio based on A_Z , line driver voltage swing, and transformer insertion loss (TIL). R_L is the line impedance, 100Ω for ADSL. $N = [(V_{LINEPP} / (2 * 11.2)] * [(1 + R_{OUT} / (R_L * A_Z)) * 10^{(TIL/20)}$
4. Calculate R_4 from R_{OUT} , A_Z , and $NR_4 = R_{OUT} / (2 * A_Z * N^2)$
5. Calculate the resistance looking into the transformer secondary (chip side). $R_{SEC} = R_L / N^2$
6. Calculate K_1 . $K_1 = (A_Z - 1) / (5.4 * A_Z)$
7. Calculate K_2 . $K_2 = R_{SEC} / (R_{SEC} + 2 * R_4)$
8. Pick a value for R_2 . Typically 3kΩ is a good value.
9. Calculate R_{EQ} . $R_{EQ} = R_2 / (1 - 5.4 * K_2)$ (Note R_{EQ} is usually negative.)
10. Calculate R_{IN} $R_{IN} = [(K_1 * R_2) / (1 - K_1) * 10k] / [10k - (K_1 * R_2) / (1 - K_1)]$
11. Calculate the gain without the input voltage divider. $A_{V1} = N * 5.4 * K_2 * [(R_{EQ} / 10k) / (R_{IN} + R_{EQ} / 10k)] / (10^{TIL/20})$
12. Calculate A_{VTOTAL} the final required gain from input to the line. $A_{VTOTAL} = V_{LINERMS} / V_{INRMS}$
13. Calculate the voltage divider network of R_1 and R_3 using A_{V1} , transformer insertion loss (TIL), $R_1 = R_{IN} * [A_{V1} / (A_{VTOTAL} * 10^{TIL/20})] R_3 = (2 * R_{IN}) / [1 - (A_{VTOTAL} * 10^{TIL/20}) / A_{V1}]$

The example shown in [Figure 43](#) is designed to the following parameters:

$V_{LINERMS} = 3.13V$ (19.8 dBm output power)

$A_Z = 4.5$

$R_{OUT} = 65\Omega$ (13.5dB return loss)

Crest Factor = 5.8 @ nominal 12V supply

Transformer Insertion Loss = 0.4dB

$V_{INRMS} = 350mV$ (AFE output level)

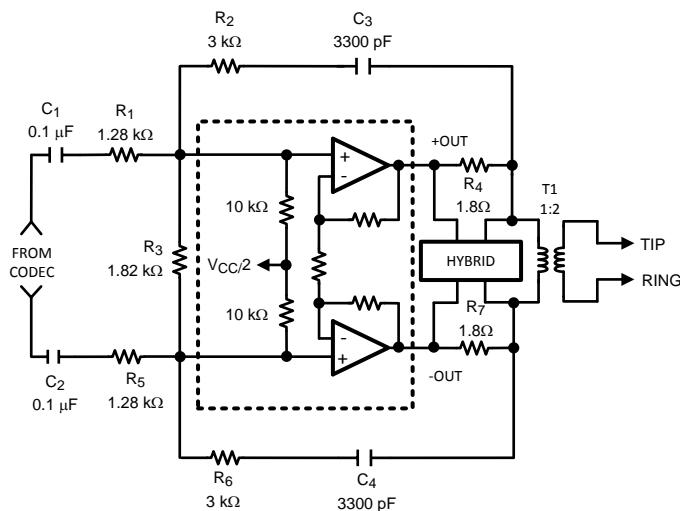


Figure 43. Active Termination Application

POWER CONSUMPTION

Power consumption is a function of line power and dynamic bias current of the line driver. After the transformer turns ratio has been selected as described above, power consumption per channel for the typical R-C termination application can be estimated as follows:

$$I_{CC} = I_{dB} + I_{LOAD} \quad (3)$$

$$I_{dB} = 0.25 * I_q \quad (4)$$

This is because 25% of the total dc current flows in the output transistors. This term effectively vanishes when the class AB stage is driven by a heavy load.

Where I_{LOAD} = average load current driven by output transistors

I_{dB} = dynamic V_{CC} bias current while driving full load power

I_{CC} = average V_{CC} current

When losses included, 103.5 mW is delivered by the driver, therefore

$$I_{RMS} = TR * \sqrt{(.1035/100)} = 32.2 \text{ mA} \quad (5)$$

Since the ADSL signal is DMT and is effectively gaussian, the average value of the supply current due to driving the load is given by

$$I_{LOAD} = \text{average} |I_{RMS}| = \sqrt{2/\pi} * I_{RMS} = 0.8 * I_{RMS} = 44.6 \text{ mA for } TR = 1.73 \quad (6)$$

Assuming 2/3 power mode, $I_{fixed} = 0.25 * 11 \text{ mA} = 2.75 \text{ mA}$

$$I_{CC} = 2.75 \text{ mA} + 44.6 \text{ mA} = 47.4 \text{ mA} \quad (7)$$

$$P_{CC} = I_{CC} * V_{CC} = 569 \text{ mW} \quad (8)$$

To get the I_{DD} full current, simply add 0.75 mA to the quiescent current per channel:

$$I_{DD} = 0.75 + 5.5 + 0.6 = 6.8 \text{ mA} \quad (9)$$

$$P_{DD} = V_{DD} * I_{DD} = 23 \text{ mW} \quad (10)$$

For the total power consumption per channel,

$$P_{CON} = P_{DD} + P_{CC} = 592 \text{ mW} \quad (11)$$

For power dissipation of the LMH6678, subtract the power into the load plus external losses:

$$P_{DISS} = 592 - 103 = 489 \text{ mW per channel} \quad (12)$$

$$P_{DISS} \text{ total} = 2 * 489 = 978 \text{ mW for both channels} \quad (13)$$

Proper selection of the external resistor between the ADJ pin can optimize the trade-off between power consumption and distortion. This external resistor will reduce the supply current for the 1/3, 2/3 and full bias settings for both channels. The approximate equation is

$$I_S = I_S * (1 - (V_{CC} - 0.8) / (30\mu A * R_{ADJ})) \quad (14)$$

Curves of V_{CC} and V_{DD} supply currents per channel vs. R_{ADJ} for the various power settings are shown in [Typical Performance Characteristics](#) section.

PACKAGE AND LAYOUT CONSIDERATION

The LMH6678 uses the 24-pin Leadless Leadframe Package, a thermally enhanced, standard size IC package designed to eliminate the use of bulky heatsinks traditionally used in thermal packages. This package can be easily mounted using standard PCB surface mount assembly techniques.

The LLP is designed so that the thermal pad is exposed on the bottom of the IC, as shown in the package drawing. This provides an extremely low thermal resistance (θ_{JC}) path between the die and the exterior of the package. The thermal pad on the bottom of the IC can then be soldered directly to the PCB, using the PCB as a heatsink. In addition, plated-through holes (vias) on the PCB provide a low thermal resistance heat flow path to the backside of the circuit board.

LAND PATTERN AND ASSEMBLY GUIDELINE FOR LMH6678

1. The thermal pad must be connected to analog ground AGND in LMH6678.
2. Prepare the PCB with a top-side land pattern, as shown in [Figure 44](#).
3. Place the recommended number of plated-through holes in the area of the thermal pad. These holes should be 8 mils max. in diameter. They are kept small so that solder wicking through the holes is not a problem during reflow. The minimum recommended number of holes for the 24-pin LLP is six, as shown in [Figure 44](#).
4. Connect all holes to the internal and bottom analog ground plane.
5. When laying out these holes to the ground plane, do not use the typical web or spoke via connection methodology, as shown in [Figure 45](#). Web connections have a high thermal resistance connection that is useful for slowing the heat transfer during soldering operations. This makes soldering the vias that have ground plane connections easier. However, in this application, low thermal resistance is desired for the most efficient heat transfer. Therefore, the holes under the thermal pad should make their connection to the internal ground plane with a complete connection around the entire circumference of the plated-through hole. Use plated via with solid connection to plane as shown in [Figure 46](#).
6. The top-side solder mask should leave the terminals of the pad connections and the thermal pad area exposed. The thermal pad area should leave the 8 mils holes exposed.
7. Apply solder paste to the exposed thermal pad area and all of the package terminals.
8. With these preparatory steps in place, the LLP is simply placed in position and run through the solder reflow operation as any standard surface-mount component. This results in a part that is properly installed.

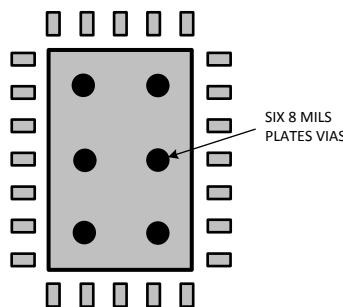


Figure 44. Recommended Land Pattern

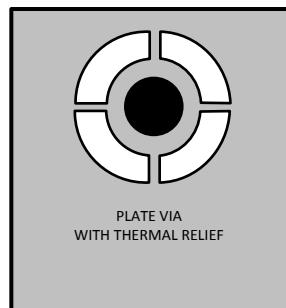


Figure 45. Via Connection Not Recommended Under the Thermal Pad

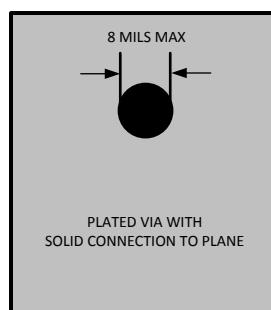


Figure 46. Via Connection Recommended For Use in Thermal Pad

HIGH SPEED DRIVER LAYOUT GUIDELINES

The LMH6678 is a high performance differential line amplifier that requires proper layout for best performance.

- Keep power-supply leads as short as possible. This will keep inductance low and resistive losses at a minimum.
- Proper power-supply bypassing with low ESR capacitors is essential to achieve good performance. A parallel combination of small (around 0.1 μ F) ceramic and bigger (6.8 μ F) tantalum bypass capacitors will provide low and impedance over a wide frequency range.
- Bypass capacitor should be placed as close as possible, limited by pick and place machine requirement, to the power-supply pins of the LMH6678 (ceramic cap first and then tantalum cap).
- PCB traces conducting high currents, such as from output to load or from power-supply connector to the power-supply pins of the LMH6678 should be kept as wide and short as possible to minimize inductance and resistive loss.
- The six holes in the landing pattern for the LMH6678 are for the thermal vias that connect the thermal pad of LLP package to the internal/external ground plane on the PCB.

For detail information on the LLP package including thermal modeling considerations and prepared procedures, please see Texas Instruments.

"Applications Note 1187: Leadless Leadframe Package (LLP)" at www.ti.com

REVISION HISTORY

Changes from Revision A (April 2013) to Revision B	Page
• Changed layout of National Data Sheet to TI format	19

IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services per JESD46, latest issue, and to discontinue any product or service per JESD48, latest issue. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All semiconductor products (also referred to herein as "components") are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its components to the specifications applicable at the time of sale, in accordance with the warranty in TI's terms and conditions of sale of semiconductor products. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by applicable law, testing of all parameters of each component is not necessarily performed.

TI assumes no liability for applications assistance or the design of Buyers' products. Buyers are responsible for their products and applications using TI components. To minimize the risks associated with Buyers' products and applications, Buyers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI components or services are used. Information published by TI regarding third-party products or services does not constitute a license to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of significant portions of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI components or services with statements different from or beyond the parameters stated by TI for that component or service voids all express and any implied warranties for the associated TI component or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Buyer acknowledges and agrees that it is solely responsible for compliance with all legal, regulatory and safety-related requirements concerning its products, and any use of TI components in its applications, notwithstanding any applications-related information or support that may be provided by TI. Buyer represents and agrees that it has all the necessary expertise to create and implement safeguards which anticipate dangerous consequences of failures, monitor failures and their consequences, lessen the likelihood of failures that might cause harm and take appropriate remedial actions. Buyer will fully indemnify TI and its representatives against any damages arising out of the use of any TI components in safety-critical applications.

In some cases, TI components may be promoted specifically to facilitate safety-related applications. With such components, TI's goal is to help enable customers to design and create their own end-product solutions that meet applicable functional safety standards and requirements. Nonetheless, such components are subject to these terms.

No TI components are authorized for use in FDA Class III (or similar life-critical medical equipment) unless authorized officers of the parties have executed a special agreement specifically governing such use.

Only those TI components which TI has specifically designated as military grade or "enhanced plastic" are designed and intended for use in military/aerospace applications or environments. Buyer acknowledges and agrees that any military or aerospace use of TI components which have **not** been so designated is solely at the Buyer's risk, and that Buyer is solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI has specifically designated certain components as meeting ISO/TS16949 requirements, mainly for automotive use. In any case of use of non-designated products, TI will not be responsible for any failure to meet ISO/TS16949.

Products	Applications
Audio	www.ti.com/audio
Amplifiers	amplifier.ti.com
Data Converters	dataconverter.ti.com
DLP® Products	www.dlp.com
DSP	dsp.ti.com
Clocks and Timers	www.ti.com/clocks
Interface	interface.ti.com
Logic	logic.ti.com
Power Mgmt	power.ti.com
Microcontrollers	microcontroller.ti.com
RFID	www.ti-rfid.com
OMAP Applications Processors	www.ti.com/omap
Wireless Connectivity	www.ti.com/wirelessconnectivity
	TI E2E Community
	e2e.ti.com